

3 A Schottky Barrier Rectifier

DESCRIPTION

This UPS360e3 in the Powermite3® package is a high efficiency Schottky rectifier that is also RoHS compliant offering high current/power capabilities previously found only in much larger packages. They are ideal for SMD applications that operate at high frequencies. In addition to its size advantages, the Powermite3® package includes a full metallic bottom that eliminates the possibility of solder flux entrapment during assembly and a unique locking tab act as an efficient heat path to the heat-sink mounting. Its innovative design makes this device ideal for use with automatic insertion equipment.

IMPORTANT: For the most current data, consult MICROSEMI's website: http://www.microsemi.com

ABSOLUTE MAXIMUM RATINGS AT 25° C (UNLESS OTHERWISE SPECIFIED)

| | | • | |
|--|--|--------------------------|------|
| Rating | Symbol | Value | Unit |
| Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage | $egin{array}{c} egin{array}{c} egin{array}{c} V_{RMM} \ V_{R} \end{array}$ | 60 | V |
| RMS Reverse Voltage | V _{R (RMS)} | 42 | V |
| Average Rectified Output Current | Io | 3 | Α |
| Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine wave Superimposed on Rated Load | I _{FSM} | 100 @ 25°C 50 @ 100°C | А |
| Storage Temperature | T_{STG} | -55 to +150 | °C |
| Junction Temperature | T_J | -55 to +125 | °C |

THERMAL CHARACTERISTICS

| Thermal Resistance | • | | |
|---------------------------|------------------|-----|----------|
| Junction-to-case (bottom) | R _{eJC} | 3.2 | °C/ Watt |
| Junction to ambient (1) | $R_{\theta JA}$ | 65 | °C/ Watt |

(1) When mounted on FR-4 PC board using 2 oz copper with recommended minimum foot print

K A 22

Powermite 3™

KEY FEATURES

- Very low thermal resistance package
- RoHS Compliant with e3 suffix part number
- Guard-ring-die construction for transient protection
- Efficient heat path with Integral locking bottom metal tab
- Low forward voltage
- Full metallic bottom eliminates flux entrapment
- Compatible with automatic insertion
- Low profile-maximum height of 1mm
- Options for screening in accordance with MIL-PRF-19500 for JAN, JANTX, and JANTXV are available by adding MQ, MX, or MV prefixes respectively to part numbers. For example, designate MXUPS360e3 for a JANTX (consult factory for Tin-Lead plating).
- Optional 100% avionics screening available by adding MA prefix for 100% temperature cycle, thermal impedance and 24 hours HTRB (consult factory for Tin-Lead plating)

APPLICATIONS/BENEFITS

- Switching and Regulating Power Supplies.
- Silicon Schottky (hot carrier) rectifier for minimal reverse voltage recovery
- Elimination of reverse-recovery oscillations to reduce need for EMI filtering
- Charge Pump Circuits
- Reduces reverse recovery loss with low I_{RM}
- Small foot print

190 X 270 mils (1:1 Actual size) See mounting pad details on pg 3

MECHANICAL & PACKAGING

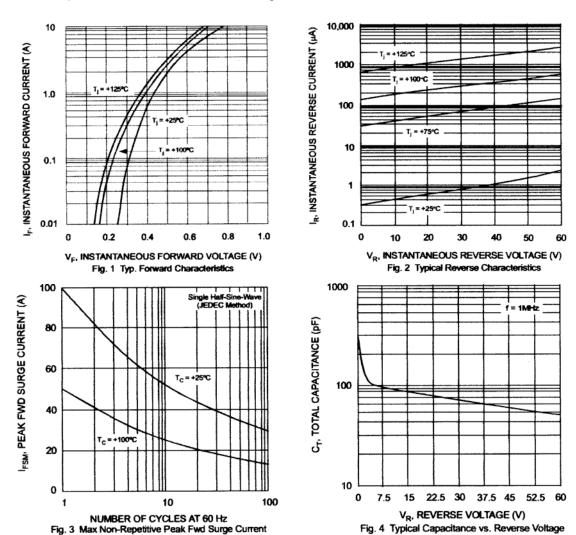
- CASE: Void-free transfer molded thermosetting epoxy compound meeting UL94V-0
- FINISH: Annealed matte-Tin plating over copper and readily solderable per MIL-STD-750 method 2026 (consult factory for Tin-Lead plating)
- POLARITY: See figure (left)
- MARKING: S360•
- WEIGHT: 0.072 gram (approx.)
- Package dimension on last page
- Tape & Reel option: 16 mm tape per Standard EIA-481-B, 5000 on 13" reel



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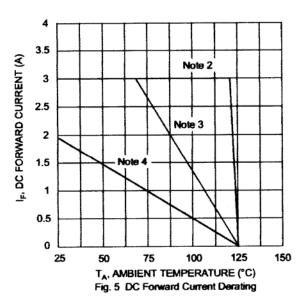
| ELECTRICAL PARAMETERS @ 25°C (unless otherwise specified) | | | | | | |
|---|----------------|---|-----|------------------------------|------------------------------|----------------|
| Parameter | Symbol | Conditions | Min | Тур. | Max | Units |
| Forward Voltage (Note 1) | V _F | $I_F = 3.5 \text{ A}$, $T_j = 25 ^{\circ}\text{C}$ $I_F = 3.5 \text{ A}$, $T_j = 125 ^{\circ}\text{C}$ $I_F = 7 ^{\circ}\text{A}$, $T_j = 25 ^{\circ}\text{C}$ $I_F = 7 ^{\circ}\text{A}$, $T_j = 25 ^{\circ}\text{C}$ | | 0.59 0.53 0.72 0.63 | 0.63 0.57 0.76 0.67 | V |
| Reverse Break Down Voltage (Note 1) | V_{BR} | I _R = 0.2 mA | 60 | | | V |
| Reverse Current (Note 1) | I _R | V _R = 60V, T _j = 25 °C V _R = 60V, T _j =100 °C V _R = 60V, T _j =125 °C | | 2 0.6 2.5 | 200 20 150 | μA mA mA |
| Capacitance | C _T | $V_R = 4 \text{ V}; f = 1 \text{ MH}_Z$ | | 130 | | pF |

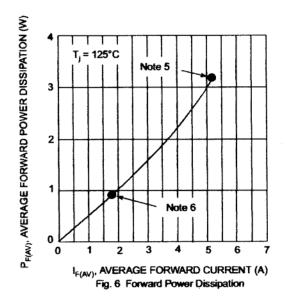
Note: 1 Short duration test pulse used to minimize self-heating effect.





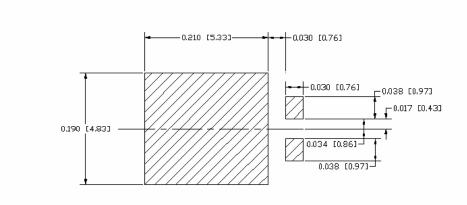
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- Notes: 2. $T_A = T_{SOLDERING\ POINT,}\ R_{\Theta JS} = 3.2^{\circ}\ C/W$ $R_{\Theta SA} = 0^{\circ}\ C/W$. 3. Device mounted on GETEK substrate, 2" x 2", 2 oz. copper , double-sided , cathode pad dimensions 0.75" x 1.0", anode pad dimensions 0.25" x 1.0". R_{OJA} in range of 20-40° C/W.
 - 4. Device mounted on FRA-4 substrate, 2" x 2", 2 oz. copper, single-sided, pad layout R_{OJA} in range of 65° C/W. See mounting pad below.
 - 5. Maximum power dissipation when the device is mounted in accordance to the conditions described in Note 3.

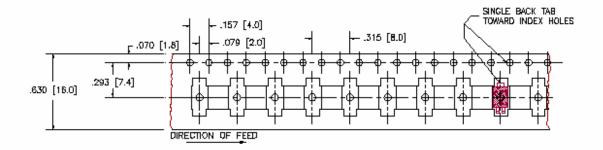
PAD LAYOUT inches [mm]



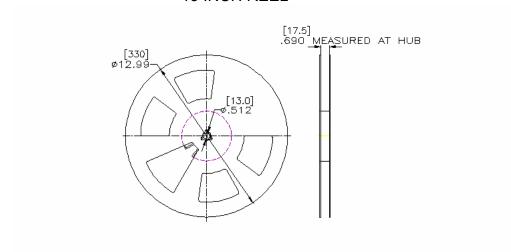


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16 mm TAPE



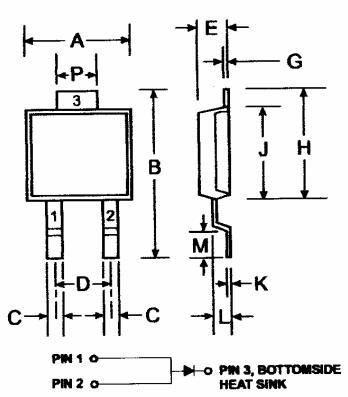
13 INCH REEL





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PACKAGE & MOUNTING PAD DIMENSIONS



| POWERMITE®3 | | | |
|----------------------|-----------------|------|--|
| Dim | M in Max | | |
| A | 4.03 | 4.09 | |
| В | 6.40 | 6.61 | |
| C | .889 NOM | | |
| D | 1.83 NOM | | |
| Ε | 1.10 | 1.14 | |
| G | .178 NOM | | |
| Н | 5.01 | 5.17 | |
| J | 4.37 | 4.43 | |
| K | .178 NOM | | |
| L | .71 | .77 | |
| M | .36 | .46 | |
| P | 1.73 | 1.83 | |
| All Dimensions in mm | | | |

Note:

Pins 1 & 2 must be electrically connected at the printed circuit board.

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